EXPERIENCE RELIABILITY

Powerex has Group A, B and C testing capabilities allowing for efficient evaluation of customer-defined specifications



Global

Power-Semiconductor

Solution

Provider

On the

Leading Edge of

Research and

Manufacturing

Technology

Powerex High Reliability Testing Experience Includes:

- Environmental
- Performance Specification Semiconductor Devices
- Soldering
- Packaging
- Calibration

- Highly Accelerated Stress Testing (H.A.S.T.)
- Test Method Standard, Electronic & Electrical Component Parts
- Electrostatic Discharge Test Methods Hybrid Semiconductor Modules

Testing Capabilities Exist for Group A, B and C Testing

Powerex has performed the following 1000, 2000, 3000, 3100, 3400, 4000 and 4200 series tests:

ENVIRONMENTAL TESTS (1000 SERIES)

1001.1	Baro	metric	pressure	(reduced)	
7077	-				

1011 Immersion

1021.2 Moisture resistance

1022.5 Resistance to solvents

1026.5 Steady-state operation life

1027.3 Steady-state operation life (sample plan)

1031.5 High temperature life (non-operating)

1032.2 High temperature (non-operating) life (sample plan)

1036.3 Intermittent operation life

1037.2 Intermittent operation life (sample plan)

1038.3 Burn-in (for diodes, rectifiers and zeners)

1039.4 Burn-in (for transistors)

Burn-in (for thyristors (controlled rectifiers))

1041.3 Salt atmosphere (corrosion)

1042.3 Burn-in and life test for power MOSFETs or insulated gate

bipolar transistors (IGBT)

1046.2 Salt spray (corrosion)

1048 Blocking life

1049 Blocking life (sample plan)

1051.5 Temperature cycling (air to air)

1056.7 Thermal Shock (liquid to liquid)

1071.5 Hermetic seal

MECHANICAL CHARACTERISTICS TESTS (2000 SERIES)

2005.2	Axial lead	tensile test	
	_		

2006 Constant acceleration

2016.2 Shock

2026.10 Solderability

2036.4 Terminal strength

2037 Bond strength

2046.1 Vibration fatigue

2056 Vibration, variable frequency

2057.1 Vibration, variable frequency (monitored)

2066 Physical dimensions

2069 Pre-cap visual, power MOSFETs

2071.3 Visual and mechanical examination2072.5 Internal visual transistor (pre-cap) inspection

2073 Visual inspection for die (semiconductor diode)

2075 Decap internal visual design verification

2076.2 Radiography

ELECTRICAL CHARACTERISTICS TESTS FOR BIPOLAR TRANSISTORS (3000 SERIES)

3001.1 Breakdown voltage, collector to base

3011.2 Breakdown voltage, collector to emitter

3026.1 Breakdown voltage, emitter to base

3030 Collector to emitter voltage

3036.1 Collector to base cutoff current

3041.1 Collector to emitter cutoff current

CIRCUIT-PERFORMANCE AND THERMAL RESISTANCE MEASUREMENTS (3100 SERIES)

3101.2 Thermal impedance testing of diodes

3103 Thermal impedance measurement for insulated gate bipolar

transistor (delta gate-emitter on voltage method)

3181 Thermal resistance for thyristors

ELECTRICAL CHARACTERISTICS TESTS FOR MOS FIELD-EFFECT TRANSISTORS (3400 SERIES)

3401.1 Breakdown voltage, gate to source

3403.1 Gate to source voltage or current

3404 MOSFET threshold voltage

3405.1 Drain to source on-state voltage

3407.1 Breakdown voltage, drain to source

3411.1 Gate reverse current

3413.1 Drain current3415.1 Drain reverse current

ELECTRICAL CHARACTERISTICS TESTS FOR DIODES

(4000 SERIES)

4011.4 Forward voltage
4016.3 Reverse current leakage

4016.3 Reverse current leakage4021.2 Breakdown voltage (diodes)

4023 Scope display

4066.3 Surge current

ELECTRICAL CHARACTERISTICS TESTS FOR THYRISTORS (CONTROLLED RECTIFIERS) (4200 SERIES)

4201.2 Holding current

4206.1 Forward blocking current

4211.1 Reverse blocking current

4216 Pulse response

4219 Reverse gate current

4221.1 Gate-trigger voltage or gate-trigger current

4223 Gate-controlled turn-on time

4224 Circuit-commutated turn-off time

4225 Gate-controlled turn-off time 4226.1 Forward "on" voltage

4231.2 Exponential rate of voltage rise



Call the Power Line at 1-800-451-1415



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